● :

1. (CTR: . 50% I_F=5mA, V_{CE}=5V)
2. (V_{ISO}=5,000Vrms)
3. (tr: TYP. 4μs V_{CE}=2V, I_C=2mA, R_L=100 Ω)
4. UL (.E236324)
5. CSA (.218896)
6. VDE (.40007240)
7. TUV (.R50029014)

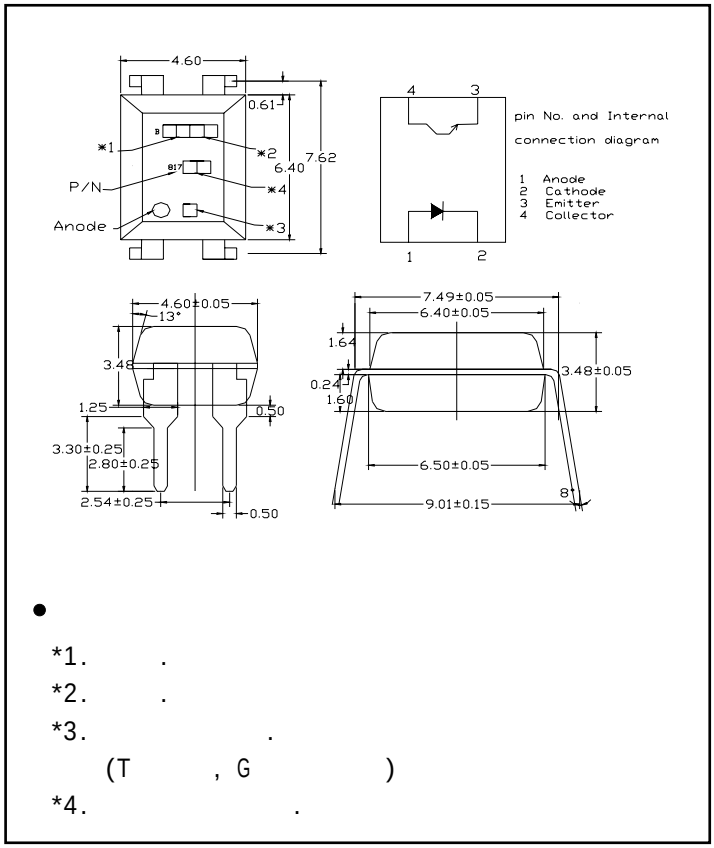
●

1. BPC-817 GaAs NPN
2. BPC-817 BIN 2.54mm

● :

1. .
2. , .
3. , , .
4. , , .
5. .

●



●

*1. .
*2. .
*3. .
(T , G)
*4. .

● (=25)

		I_F	50	mA
		V_R	6	V
		P	70	mW
		V_{CEO}	35	V
		V_{ECO}	6	
		I_C	50	mA
		P_C	150	mW
		P_{tot}	200	mW
*1		V_{iso}	5,000	Vrms
		V_{IOTM}	6,000	V
		V_{IORM}	630	V
		T_{opr}	-30 to + 100	
		T_{stg}	-55 to + 125	
*2		Tsol	260	

*1. , . =40~60%
.
(1)
(2)
(3) .

*2. 10

● (=25)

				.	.		
		V_F	I_F=20mA	---	1.2	1.4	V
		I_R	V_R=4V	---	---	10	μA
		C_t	V=0, f=1KHz	---	30	250	pF
		I_{CEO}	V_{CE}=20V, I_F=0	---	---	100	nA
		BV_{CEO}	I_C=0.1mA I_F=0	35	---	---	V
		BV_{ECO}	I_E=10μA I_F=0	6	---	---	V
		I_c	I_F=5mA	2.5	---	30	mA
	*1	CTR	V_{CE}=5V	50	---	600	%
		$V_{CE(sat)}$	I_F=20mA I_C= 1mA	---	0.1	0.2	V
		R_{iso}	DC500V 40~60%R.H.	5×10^{10}	1×10^{11}	---	Ω
		C_f	V=0, f=1MHz	---	0.6	1	pF
		f_c	V_{CE}=5V, I_C=2mA R_L=100Ω, -3dB	---	80	---	kHz
		t_r	V_{CE}=2V, I_C=2mA	---	4	18	μs
		t_f	R_L=100Ω	---	3	18	μs

*1 = I_C / I_F × 100%

●

	. (%)	. (%)
L	50	100
A	80	160
B	130	260
C	200	400
D	300	600
L or A or B or C or D	50	600

:

1. : I_F=5mA, V_{CE}=5V, Ta=25 .

Fig.1 Forword Current vs. Ambient Temperatute

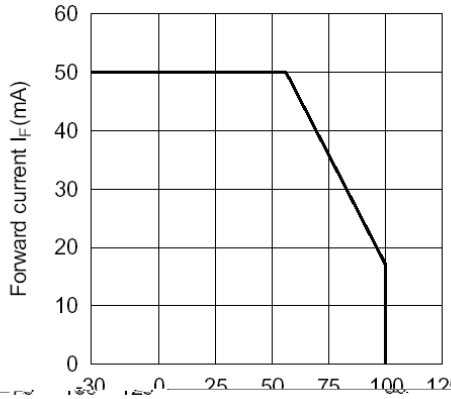
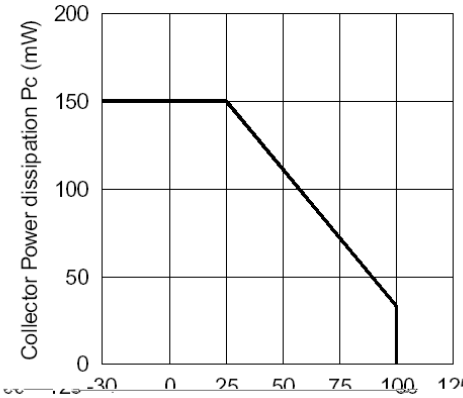


Fig.2 Collector Power Dissiption vs. Ambient Temperature



rent vs. Forward

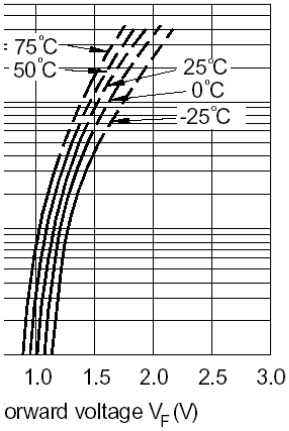


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

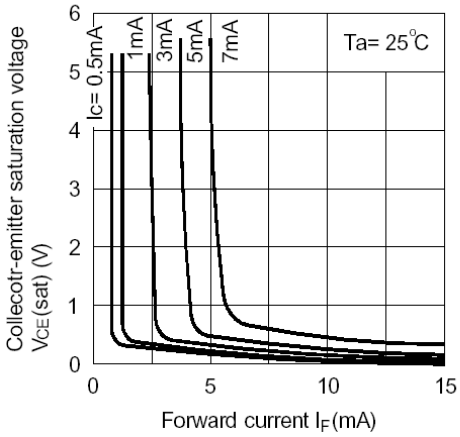
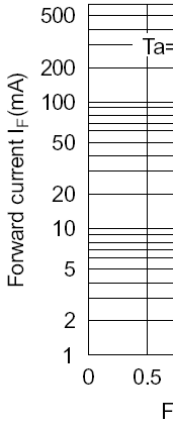


Fig.4 Forward Cur Voltage



rrent vs. itter Voltage

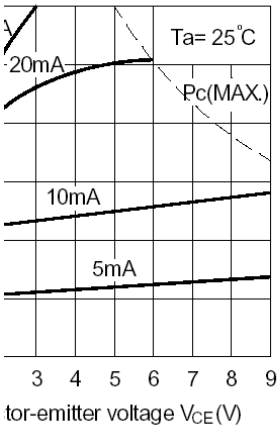


Fig.5 Current Transfer Ratio vs. Forward Current

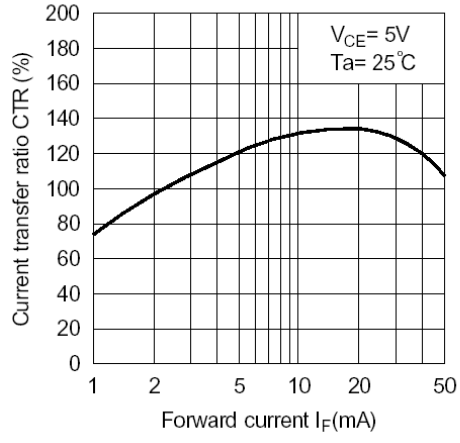


Fig.6 Collector Cu Collector-em

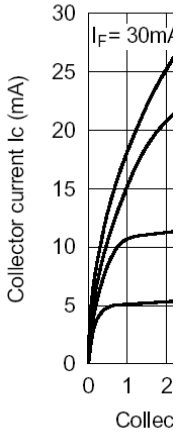


Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

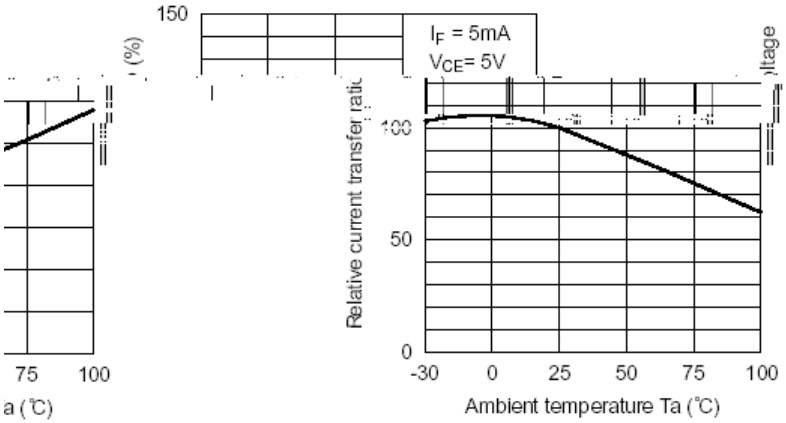


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

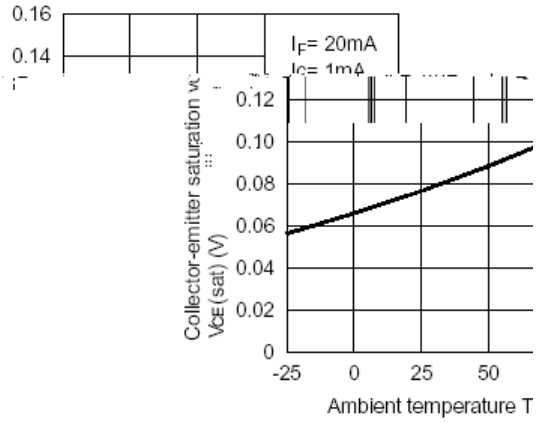


Fig.9 Collector Dark Current vs. Ambient Temperature

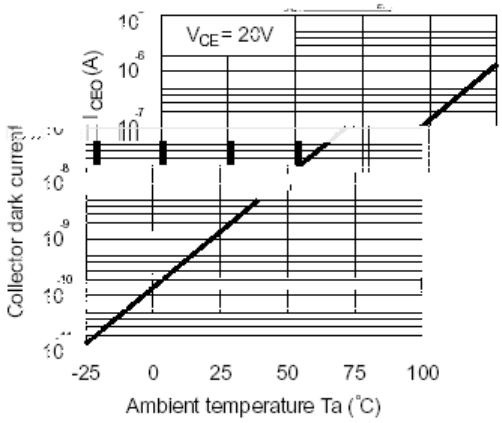


Fig.10 Response Time vs. Load Resistance

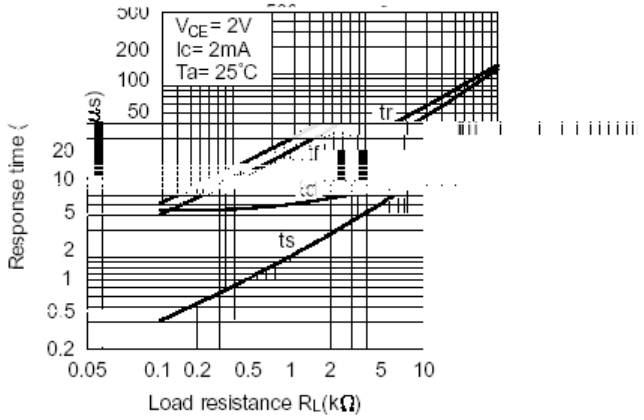
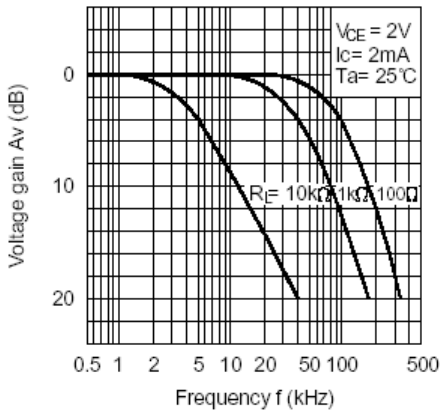
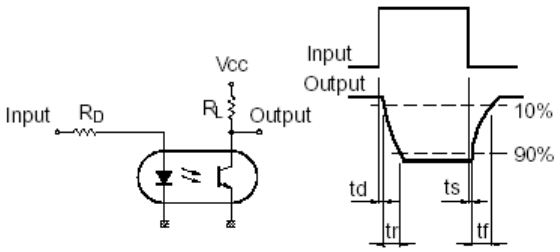


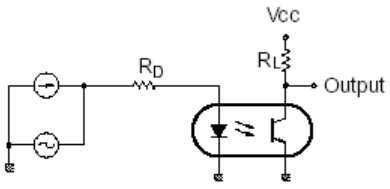
Fig.11 Frequency Response



Test Circuit for Response Time



Test Circuit for Frequency Response



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		MIL-STD-750:1026 MIL-STD-883:1005 JIS C 7021 :B-1	If=50mA 1000	0/20

č ȳ z C 7021 :B-1